

Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 116916		APPLICATION NO. New US Application	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANTS Takamitsu HIGUCHI et al. FILING DATE August 21, 2003			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	
DV	1	6,232,242 B1	05/15/2001	Hata et al.	_____	_____	
	2	5,155,658	10/13/1992	Inam et al.	_____	_____	
	3	5,173,474	12/22/1992	Connell et al.	_____	_____	
	4	5,270,298	12/14/1993	Ramesh	_____	_____	
	5	5,358,925	10/25/1994	Neville Connell et al.	_____	_____	
	6	5,416,062	05/16/1995	Harada et al.	_____	_____	
	7	5,801,105	09/01/1998	Yano et al.	_____	_____	
	8	5,810,923	09/22/1998	Yano et al.	_____	_____	
	9	5,828,080	10/27/1998	Yano et al.	_____	_____	
	10	6,045,626	04/04/2000	Yano et al.	_____	_____	
	11	6,096,434	08/01/2000	Yano et al.	_____	_____	
DV	12	6,121,647	09/19/2000	Yano et al.	_____	_____	
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	
DV	13	JP A 2000-332569 (with abstract and translation)	11/30/2000	Japan	_____	_____	
	14	JP A 2001-077102 (with abstract and translation)	03/23/2001	Japan	_____	_____	
	15	JP A 6-097452 (with abstract and translation)	04/08/1994	Japan	_____	_____	
	16	JP A 8-109099 (with abstract and translation)	04/30/1996	Japan	_____	_____	
	17	JP A 8-255790 (with abstract and translation)	10/01/1996	Japan	_____	_____	
	18	JP A 8-264524 (with abstract and translation)	10/11/1996	Japan	_____	_____	
	19	JP A 9-110592 (with abstract and translation)	04/28/1997	Japan	_____	_____	
DV	20	JP A 10-017394 (with abstract and translation)	01/20/1998	Japan	_____	_____	
EXAMINER <i>gfeland</i>				DATE CONSIDERED 12/18/04			
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DV	21	JP A 9-263494 (with abstract and translation)	10/07/1997	Japan		
	22	JP A 10-107216 (with abstract and translation)	04/24/1998	Japan		
	23	JP A 11-026296 (with abstract and translation)	01/29/1999	Japan		
	24	JP A 2000-101345 (with abstract and translation)	04/07/2000	Japan		
	25	JP A 2002-009358 (with abstract and translation)	01/11/2002	Japan		
	26	JP A 2001-122698 (with abstract and translation)	05/08/2001	Japan		
DV	27	JP A 10-265948 (with abstract and translation)	10/06/1998	Japan		
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)						
DV	28	Fork et al., "Epitaxial yttria-stabilized zirconia on hydrogen-terminated Si by pulsed laser deposition", Appl. Phys. Letter 57, September 10, 1990, pp 1137-1139				
DV	29	Haakenaasen et al., "High quality crystalline $\text{YBa}_2\text{Cu}_3\text{O}_{7.5}$ films on thin silicon substrates", Appl. Phys. Lett. 64, March 21, 1994, pp 1573-1575				
DV	30	Hou et al., "Structure and properties of epitaxial $\text{Ba}_{0.5}\text{Sr}_{0.5}\text{TiO}_3/\text{SrRuO}_3/\text{ZrO}_2$ heterostructure on Si grown by off-axis sputtering", Appl. Phys. Lett. 67, September 4, 1995, pp 1387-1389				
EXAMINER <i>ghuland</i>				DATE CONSIDERED 12/18/04		
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